

Huan-Lin Chang

List of Publications by Year in descending order

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514
citing authors

#	ARTICLE	IF	CITATIONS
1	Engineering Negative Differential Resistance in NCFETs for Analog Applications. IEEE Transactions on Electron Devices, 2018, 65, 2033-2039.	3.0	79
2	Compact models of negative-capacitance FinFETs: Lumped and distributed charge models. , 2016, , .		69
3	Stress-Induced Hump Effects of p-Channel Polycrystalline Silicon Thin-Film Transistors. IEEE Electron Device Letters, 2008, 29, 1332-1335.	3.9	66
4	Designing 0.5 V 5-nm HP and 0.23 V 5-nm LP NC-FinFETs With Improved OFF_{OFF} Sensitivity in Presence of Parasitic Capacitance. IEEE Transactions on Electron Devices, 2018, 65, 1211-1216.	3.0	31
5	Variation Caused by Spatial Distribution of Dielectric and Ferroelectric Grains in a Negative Capacitance Field-Effect Transistor. IEEE Transactions on Electron Devices, 2018, 65, 4652-4658.	3.0	29
6	BSIM-HV: High-Voltage MOSFET Model Including Quasi-Saturation and Self-Heating Effect. IEEE Transactions on Electron Devices, 2019, 66, 4258-4263.	3.0	23
7	A Predictive Tunnel FET Compact Model With Atomistic Simulation Validation. IEEE Transactions on Electron Devices, 2017, 64, 599-605.	3.0	20
8	Modeling of Advanced RF Bulk FinFETs. IEEE Electron Device Letters, 2018, 39, 791-794.	3.9	17
9	Modeling of Subsurface Leakage Current in Low Short Channel MOSFET at Accumulation Bias. IEEE Transactions on Electron Devices, 2016, 63, 1840-1845.	3.0	14
10	Effect of Polycrystallinity and Presence of Dielectric Phases on NC-FinFET Variability. , 2018, , .		14
11	Compact Modeling Source-to-Drain Tunneling in Sub-10-nm GAA FinFET With Industry Standard Model. IEEE Transactions on Electron Devices, 2017, 64, 3576-3581.	3.0	13
12	Coupling Effects of Dual SiGe Power Amplifiers for 802.11n MIMO Applications. , 0, , .		11
13	Physical mechanism of HfO ₂ -based bipolar resistive random access memory. , 2011, , .		11
14	Modeling of Back-Gate Effects on Gate-Induced Drain Leakage and Gate Currents in UTB SOI MOSFETs. IEEE Transactions on Electron Devices, 2017, 64, 3986-3990.	3.0	9
15	Negative-Capacitance FinFETs: Numerical Simulation, Compact Modeling and Circuit Evaluation. , 2018, , .		9
16	Improved SPICE macromodel of phase change random access memory. , 2009, , .		6
17	Modeling of GeOI and validation with Ge-CMOS inverter circuit using BSIM-IMG industry standard model. , 2016, , .		6
18	Predictive effective mobility model for FDSOI transistors using technology parameters. , 2016, , .		6

#	ARTICLE	IF	CITATIONS
19	Modeling of threshold voltage for operating point using industry standard BSIM-IMG model. , 2016, , .		6
20	New Mobility Model for Accurate Modeling of Transconductance in FDSOI MOSFETs. IEEE Transactions on Electron Devices, 2018, 65, 463-469.	3.0	5
21	A parameterized SPICE macromodel of resistive random access memory and circuit demonstration. , 2011, , .		3
22	Voltage Linearity Improvement of HfO ₂ -Based Metal-Insulator-Metal Capacitors with H ₂ O Prepulse Treatment. Journal of the Electrochemical Society, 2011, 158, H128.	2.9	3
23	Performance Enhancement of the nMOSFET Low-Noise Amplifier by Package Strain. IEEE Transactions on Electron Devices, 2007, 54, 160-162.	3.0	1
24	Differential power combining technique for general power amplifiers using lumped component network. , 2006, , .		0
25	Reduction of Crosstalk Between Dual Power Amplifiers Using Laser Treatment. IEEE Microwave and Wireless Components Letters, 2008, 18, 602-604.	3.2	0
26	Core Model for Independent Multigate MOSFETs. , 2019, , 15-34.		0